

TOSHIBA GTR MODULE SILICON N CHANNEL IGBT

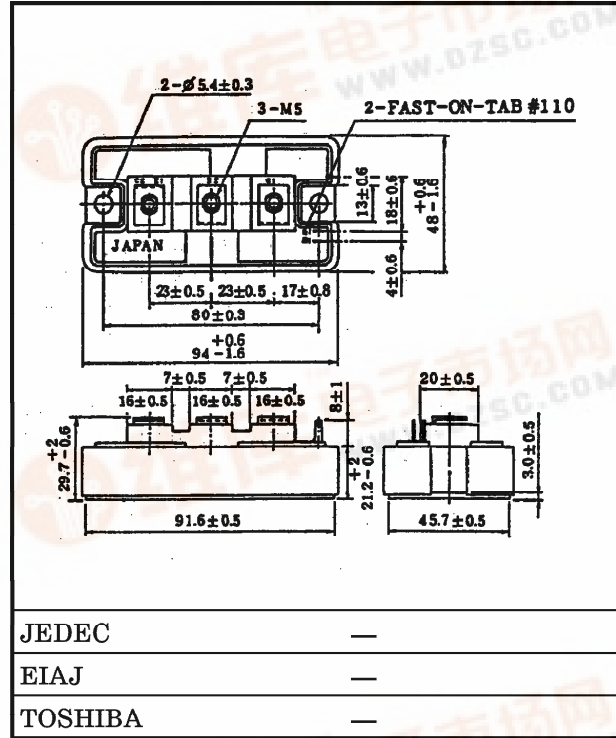
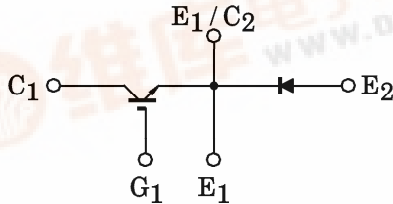
MG150J1JS50

HIGH POWER SWITCHING APPLICATIONS.
MOTOR CONTROL APPLICATIONS.

Unit in mm

- The Electrodes are Isolated from Case.
- High Input Impedance
- Includes a Complete Half Bridge in One Package.
- Enhancement-Mode
- High Speed : $t_f = 0.30\mu s$ (Max.) ($I_C = 150A$)
 $t_{rr} = 0.15\mu s$ (Max.) ($I_F = 150A$)
- Low Saturation Voltage
: $V_{CE(sat)} = 2.70V$ (Max.) ($I_C = 150A$)

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	600	V
Gate-Emitter Voltage	V_{GES}	±20	V
Collector Current	DC	I_C	150
	1ms	I_{CP}	300
Forward Current	DC	I_F	150
	1ms	I_{FM}	300
Collector Power Dissipation (Tc = 25°C)	P_C	780	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-40~125	°C
Isolation Voltage	V_{Isol}	2500 (AC 1Min.)	V
Screw Torque (Terminal/Mounting)	—	3/3	N·m

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA
Collector Cut-off Current	I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	—	—	2.0	mA
Gate-Emitter Cut-off Voltage	$V_{GE} (off)$	$I_C = 15mA, V_{CE} = 5V$	5.0	7.0	8.0	V
Collector-Emitter Saturation Voltage	$V_{CE} (sat)$	$I_C = 150A, V_{GE} = 15V$	—	2.10	2.70	V
Input Capacitance	C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	14200	—	pF
Switching Time	Turn-on Delay Time	$t_d (on)$	—	0.15	0.30	μs
	Rise Time	t_r	—	0.15	0.30	
	Turn-on Time	t_{on}	—	0.50	1.00	
	Turn-off Delay Time	$t_d (off)$	—	0.20	0.40	
	Fall Time	t_f	—	0.15	0.30	
	Turn-off Time	t_{off}	—	0.50	1.00	
Forward Voltage	V_F	$I_F = 150A, V_{GE} = 0$	—	2.30	3.00	V
Reverse Recovery Time	t_{rr}	$I_F = 150A, V_{GE} = -10V$ $di/dt = 200A/\mu s$	—	0.08	0.15	μs
Thermal Resistance	$R_{th} (j-c)$	Transistor Stage	—	—	0.16	$^{\circ}C/W$
		Diode Stage	—	—	0.35	

Note 1 Switching Time Test Circuit & Timing Chart

